



Vincotech

10-PZ126PA025M7-P869F78Y

datasheet

flowPACK 0B

1200 V / 25 A

Topology features

- Kelvin Emitter for improved switching performance
- Temperature sensor
- Inverter

Component features

- Easy paralleling
- Low turn-off losses
- Low collector emitter saturation voltage
- Positive temperature coefficient
- Short tail current
- Switching optimized for EMC

Housing features

- Base isolation: Al_2O_3
- Clip-in, reliable mechanical connection, qualified for wave soldering
- Convex shaped substrate for superior thermal contact
- Thermo-mechanical push-and-pull force relief
- Press-fit pin
- Reliable cold welding connection

Target applications

- Industrial Drives

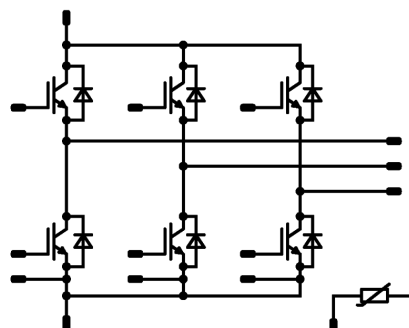
Types

- 10-PZ126PA025M7-P869F78Y

flow 0 12 mm housing



Schematic





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Maximum Ratings

$T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Inverter Switch				
Collector-emitter voltage	V_{CES}		1200	V
Collector current (DC current)	I_C	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	34	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}	50	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	82	W
Gate-emitter voltage	V_{GES}		± 20	V
Short circuit ratings	t_{SC}	$V_{GE} = 15\text{ V}$, $V_{CC} = 800\text{ V}$ $T_j = 150\text{ °C}$	9,5	μs
Maximum junction temperature	T_{jmax}		175	$^{\circ}\text{C}$

Inverter Diode

Peak repetitive reverse voltage	V_{RRM}		1200	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	33	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}	50	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	62	W
Maximum junction temperature	T_{jmax}		175	$^{\circ}\text{C}$

Module Properties

Thermal Properties

Storage temperature	T_{stg}		-40...+125	$^{\circ}\text{C}$
Operation temperature under switching condition	T_{jop}		$-40...+(T_{jmax} - 25)$	$^{\circ}\text{C}$

Isolation Properties

Isolation voltage	V_{isol}	DC Test Voltage* $t_p = 2\text{ s}$	6000	V
Creepage distance			>12,7	mm
Clearance			9,22	mm
Comparative Tracking Index	CTI		≥ 200	

*100 % tested in production



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Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	

Inverter Switch

Static

Gate-emitter threshold voltage	$V_{GE(th)}$			10	0,0025	25	5,4	6	6,6	V
Collector-emitter saturation voltage	V_{CEsat}		15		25	25 125 150		1,64 1,89 1,95	2,1 ⁽¹⁾	V
Collector-emitter cut-off current	I_{CES}		0	1200		25			70	µA
Gate-emitter leakage current	I_{GES}		20	0		25			200	nA
Internal gate resistance	r_g							None		Ω
Input capacitance	C_{ies}	0	10	25				4800		pF
Output capacitance	C_{oes}							170		pF
Reverse transfer capacitance	C_{res}							57		pF
Gate charge	Q_g	$V_{CC} = 600$ V	0/15		25	25		180		nC

Thermal

Thermal resistance junction to sink ⁽²⁾	$R_{th(j-s)}$	$\lambda_{paste} = 3,4$ W/mK (PSX)						1,16		K/W
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Dynamic

Turn-on delay time	$t_{d(on)}$	$R_{gon} = 16$ Ω $R_{goff} = 16$ Ω	±15	600	25	25 125 150		147,2 149,2 145,2		ns
Rise time	t_r					25 125 150		28,6 33,4 34		ns
Turn-off delay time	$t_{d(off)}$					25 125 150		170,6 191,4 195,6		ns
Fall time	t_f					25 125 150		95,03 109,96 114,76		ns
Turn-on energy (per pulse)	E_{on}	$Q_{tFWD}=2,54$ µC $Q_{tFWD}=3,88$ µC $Q_{tFWD}=4,28$ µC				25 125 150		2,06 2,66 2,82		mWs
Turn-off energy (per pulse)	E_{off}					25 125 150		1,67 2,18 2,29		mWs



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Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	

Inverter Diode

Static

Forward voltage	V_F				25	25 125 150		1,63 1,7 1,69	2,1 ⁽¹⁾	V
Reverse leakage current	I_R	$V_i = 1200$ V				25			35	µA

Thermal

Thermal resistance junction to sink ⁽²⁾	$R_{th(j-s)}$	$\lambda_{paste} = 3,4$ W/mK (PSX)						1,54		K/W
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Dynamic

Peak recovery current	I_{RM}	$di/dt=645$ A/µs $di/dt=673$ A/µs $di/dt=633$ A/µs	± 15	600	25	25 125 150		20,99 22,6 23,21		A
Reverse recovery time	t_{rr}					25 125 150		254,14 367,32 404,24		ns
Recovered charge	Q_r					25 125 150		2,54 3,88 4,28		µC
Reverse recovered energy	E_{rec}					25 125 150		0,884 1,45 1,61		mWs
Peak rate of fall of recovery current	$(di_{rr}/dt)_{max}$					25 125 150		217,37 134,32 132,01		A/µs



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Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	

Thermistor

Static

Rated resistance	R					25		22		kΩ
Deviation of R100	$\Delta_{R/R}$	$R_{100} = 1484 \Omega$				100	-5		5	%
Power dissipation	P					25		130		mW
Power dissipation constant	d					25		1,5		mW/K
B-value	$B_{(25/50)}$	Tol. $\pm 1 \%$						3962		K
B-value	$B_{(25/100)}$	Tol. $\pm 1 \%$						4000		K
Vincotech Thermistor Reference									I	

⁽¹⁾ Value at chip level

⁽²⁾ Only valid with pre-applied Vincotech thermal interface material.



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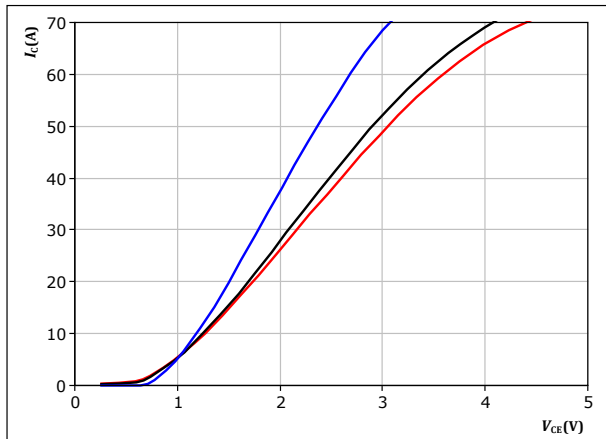
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Inverter Switch Characteristics

figure 1. IGBT

Typical output characteristics

$$I_C = f(V_{CE})$$

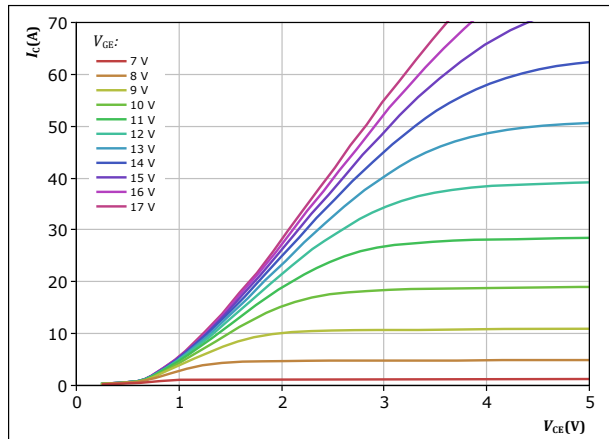


$t_p = 250 \mu s$
 $V_{GE} = 15 V$
 $T_j: 25^\circ C, 125^\circ C, 150^\circ C$

figure 2. IGBT

Typical output characteristics

$$I_C = f(V_{CE})$$

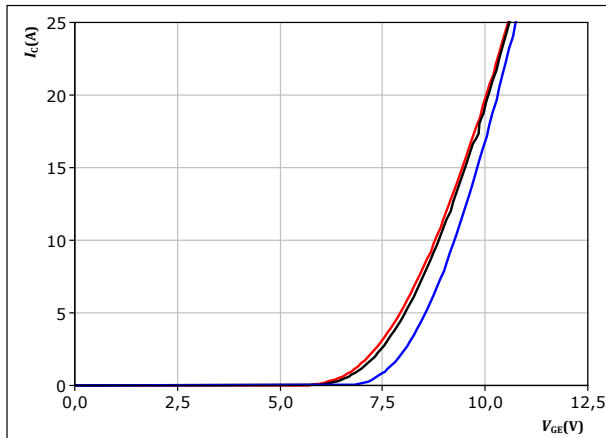


$t_p = 250 \mu s$
 $T_j = 150^\circ C$
 V_{GE} from 7 V to 17 V in steps of 1 V

figure 3. IGBT

Typical transfer characteristics

$$I_C = f(V_{GE})$$

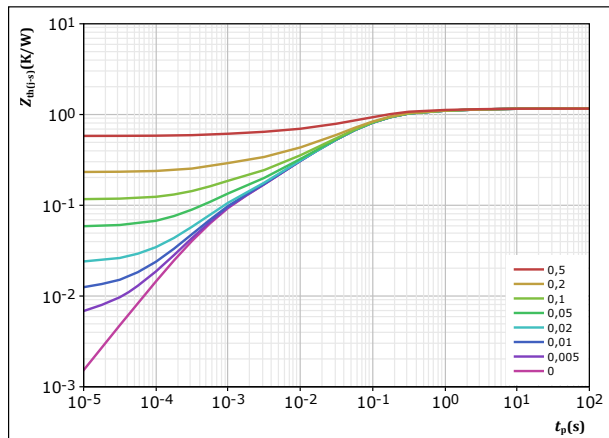


$t_p = 250 \mu s$
 $V_{CE} = 10 V$
 $T_j: 25^\circ C, 125^\circ C, 150^\circ C$

figure 4. IGBT

Transient thermal impedance as a function of pulse width

$$Z_{th(j-s)} = f(t_p)$$



$D = t_p / T$
 $R_{th(j-s)} = 1,162 K/W$
IGBT thermal model values

$R (K/W)$	$\tau (s)$
5,33E-02	3,54E+00
1,07E-01	5,75E-01
5,05E-01	1,04E-01
2,68E-01	3,30E-02
1,51E-01	7,35E-03
7,80E-02	6,52E-04



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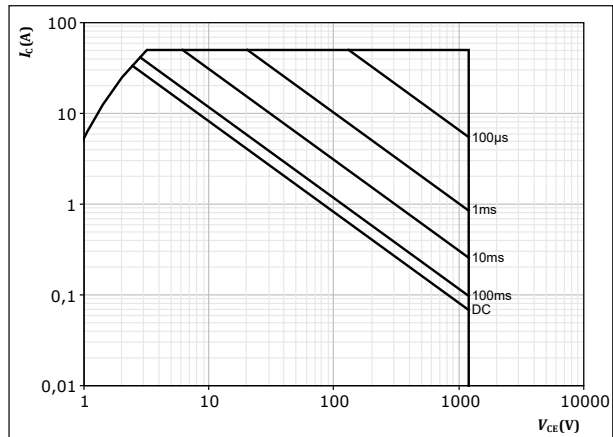
datasheet

Inverter Switch Characteristics

figure 5. IGBT

Safe operating area

$$I_C = f(V_{CE})$$



$D =$ single pulse

$T_s = 80$ °C

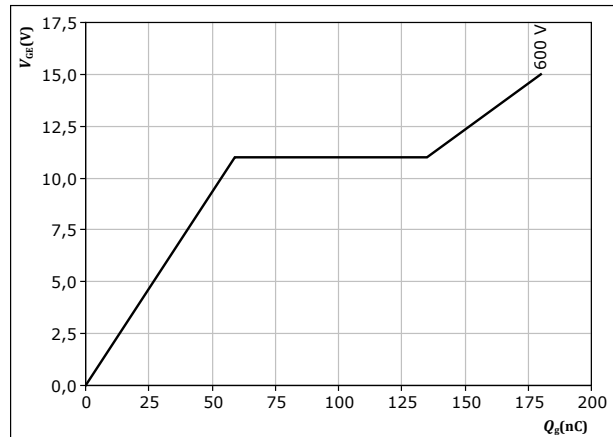
$V_{GE} = 15$ V

$T_j = T_{jmax}$

figure 6. IGBT

Gate voltage vs gate charge

$$V_{GE} = f(Q_g)$$



$I_C = 25$ A

$T_j = 25$ °C



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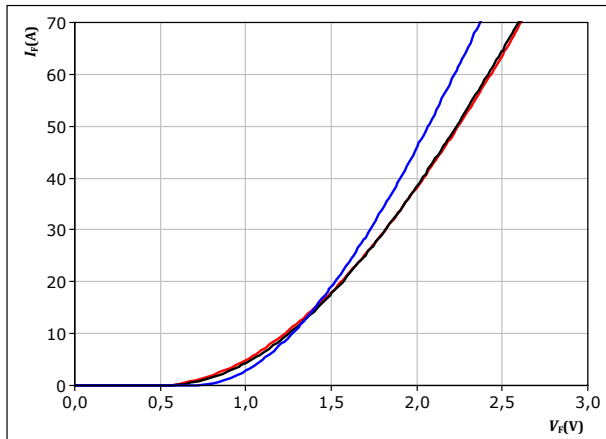
Inverter Diode Characteristics

figure 7.

FWD

Typical forward characteristics

$$I_F = f(V_F)$$



$t_p = 250 \mu s$

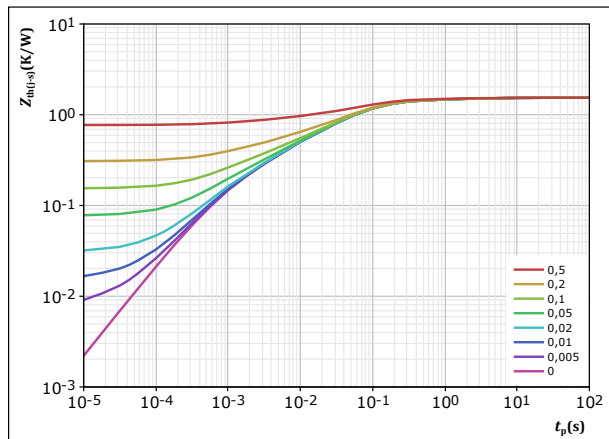
T_j :
— 25 °C
— 125 °C
— 150 °C

figure 8.

FWD

Transient thermal impedance as a function of pulse width

$$Z_{th(j-s)} = f(t_p)$$



$D = t_p / T$
 $R_{th(j-s)} = 1,539 \text{ K/W}$

FWD thermal model values

$R \text{ (K/W)}$	$\tau \text{ (s)}$
4,69E-02	5,05E+00
1,06E-01	7,09E-01
5,57E-01	1,01E-01
4,68E-01	3,22E-02
2,35E-01	5,52E-03
8,77E-02	1,01E-03
4,01E-02	5,52E-04



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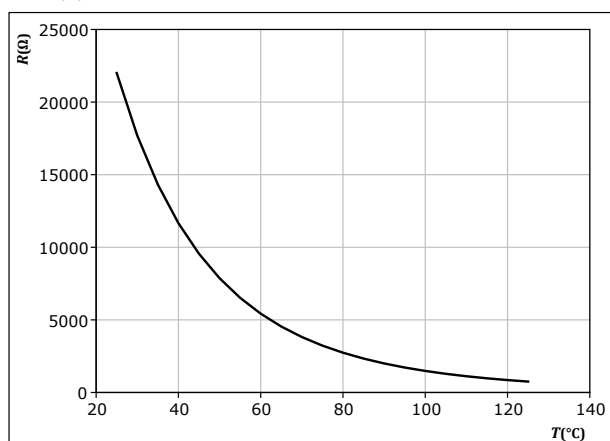
Thermistor Characteristics

figure 9.

Thermistor

Typical NTC characteristic as function of temperature

$$R_T = f(T)$$





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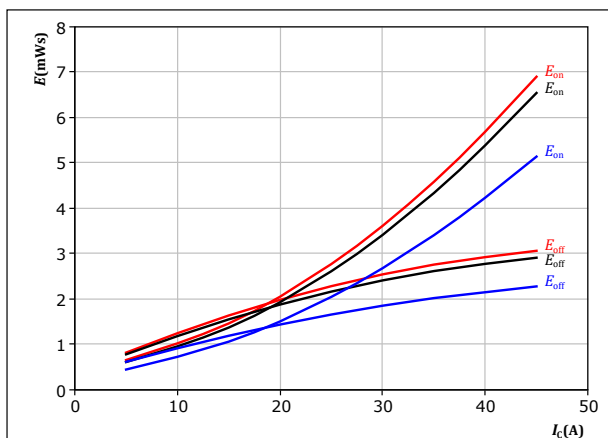
Inverter Switching Characteristics

figure 10.

IGBT

Typical switching energy losses as a function of collector current

$$E = f(I_c)$$



With an inductive load at

$V_{CE} = 600 \text{ V}$
 $V_{GE} = \pm 15 \text{ V}$
 $R_{gon} = 16 \text{ } \Omega$
 $R_{goff} = 16 \text{ } \Omega$

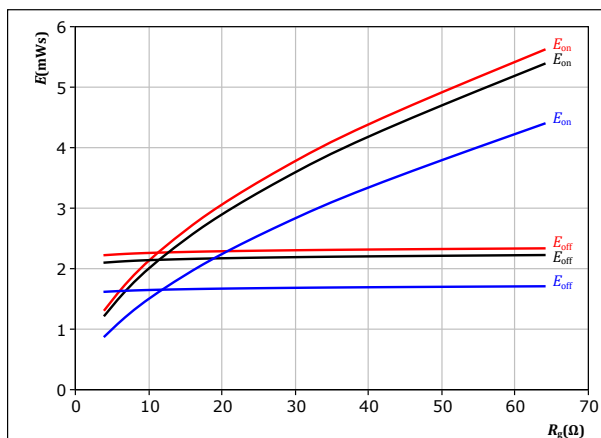
T_j :
— 25 °C
— 125 °C
— 150 °C

figure 11.

IGBT

Typical switching energy losses as a function of IGBT turn on gate resistor

$$E = f(R_g)$$



With an inductive load at

$V_{CE} = 600 \text{ V}$
 $V_{GE} = \pm 15 \text{ V}$
 $I_c = 25 \text{ A}$

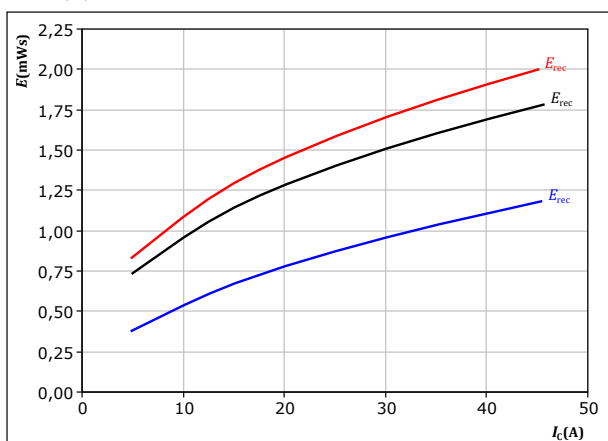
T_j :
— 25 °C
— 125 °C
— 150 °C

figure 12.

FWD

Typical reverse recovered energy loss as a function of collector current

$$E_{rec} = f(I_c)$$



With an inductive load at

$V_{CE} = 600 \text{ V}$
 $V_{GE} = \pm 15 \text{ V}$
 $R_{gon} = 16 \text{ } \Omega$

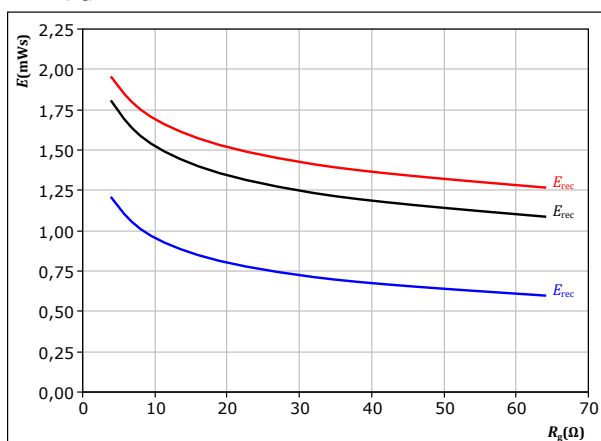
T_j :
— 25 °C
— 125 °C
— 150 °C

figure 13.

FWD

Typical reverse recovered energy loss as a function of IGBT turn on gate resistor

$$E_{rec} = f(R_g)$$



With an inductive load at

$V_{CE} = 600 \text{ V}$
 $V_{GE} = \pm 15 \text{ V}$
 $I_c = 25 \text{ A}$

T_j :
— 25 °C
— 125 °C
— 150 °C



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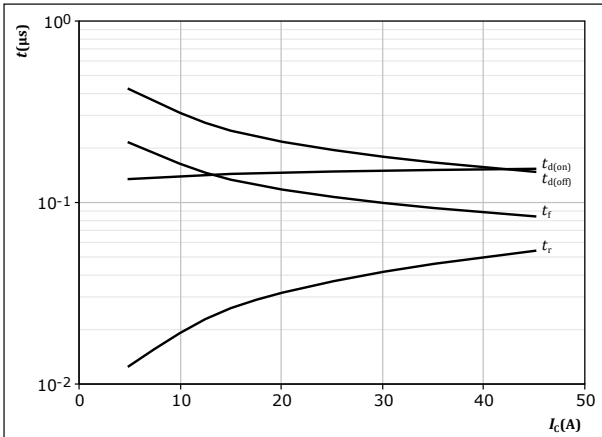
Inverter Switching Characteristics

figure 14.

IGBT

Typical switching times as a function of collector current

$$t = f(I_c)$$



With an inductive load at

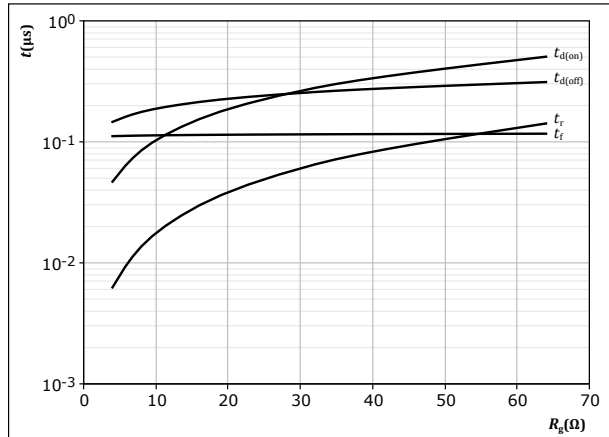
$T_j = 150$ °C
 $V_{CE} = 600$ V
 $V_{GE} = \pm 15$ V
 $R_{gon} = 16$ Ω
 $R_{goff} = 16$ Ω

figure 15.

IGBT

Typical switching times as a function of IGBT turn on gate resistor

$$t = f(R_g)$$



With an inductive load at

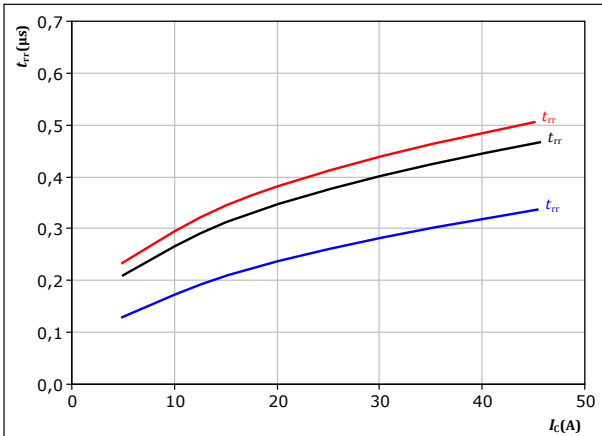
$T_j = 150$ °C
 $V_{CE} = 600$ V
 $V_{GE} = \pm 15$ V
 $I_c = 25$ A

figure 16.

FWD

Typical reverse recovery time as a function of collector current

$$t_{rr} = f(I_c)$$



With an inductive load at

$V_{CE} = 600$ V
 $V_{GE} = \pm 15$ V
 $R_{gon} = 16$ Ω

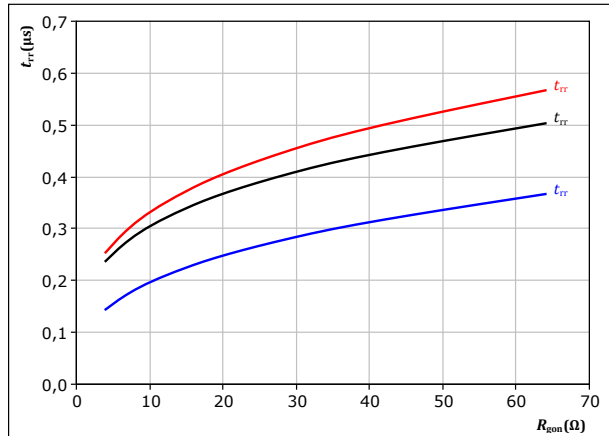
T_j : 25 °C (blue)
125 °C (black)
150 °C (red)

figure 17.

FWD

Typical reverse recovery time as a function of IGBT turn on gate resistor

$$t_{rr} = f(R_{gon})$$



With an inductive load at

$V_{CE} = 600$ V
 $V_{GE} = \pm 15$ V
 $I_c = 25$ A

T_j : 25 °C (blue)
125 °C (black)
150 °C (red)



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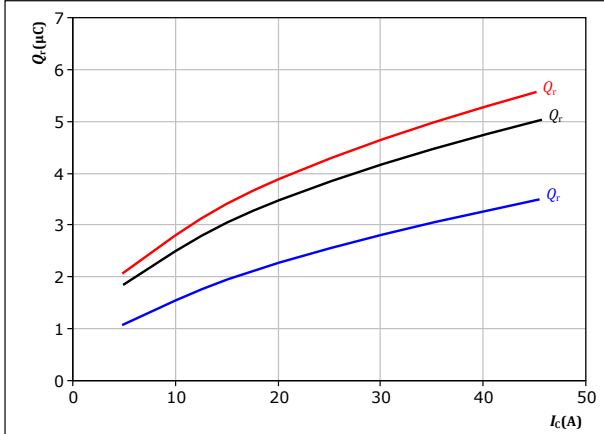
Inverter Switching Characteristics

figure 18.

FWD

Typical recovered charge as a function of collector current

$$Q_r = f(I_c)$$



With an inductive load at

$V_{CE} = 600$ V
 $V_{GE} = \pm 15$ V
 $R_{gon} = 16$ Ω

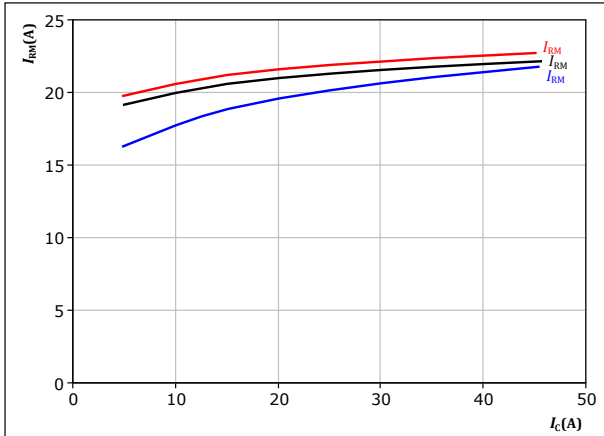
T_j :
— 25 °C
— 125 °C
— 150 °C

figure 20.

FWD

Typical peak reverse recovery current as a function of collector current

$$I_{RM} = f(I_c)$$



With an inductive load at

$V_{CE} = 600$ V
 $V_{GE} = \pm 15$ V
 $R_{gon} = 16$ Ω

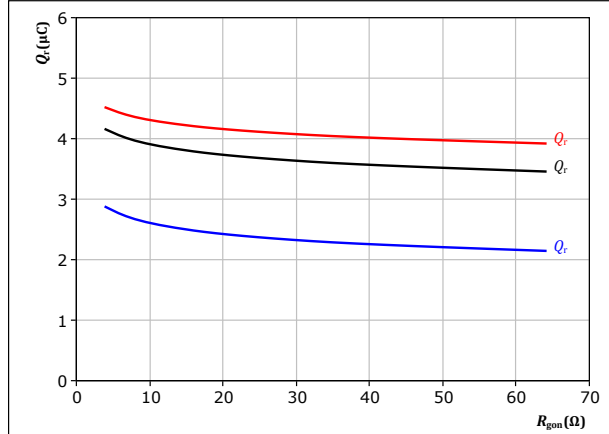
T_j :
— 25 °C
— 125 °C
— 150 °C

figure 19.

FWD

Typical recovered charge as a function of IGBT turn on gate resistor

$$Q_r = f(R_{gon})$$



With an inductive load at

$V_{CE} = 600$ V
 $V_{GE} = \pm 15$ V
 $I_c = 25$ A

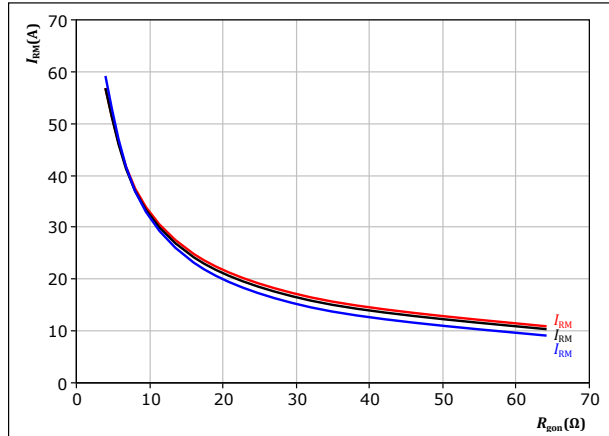
T_j :
— 25 °C
— 125 °C
— 150 °C

figure 21.

FWD

Typical peak reverse recovery current as a function of IGBT turn on gate resistor

$$I_{RM} = f(R_{gon})$$



With an inductive load at

$V_{CE} = 600$ V
 $V_{GE} = \pm 15$ V
 $I_c = 25$ A

T_j :
— 25 °C
— 125 °C
— 150 °C



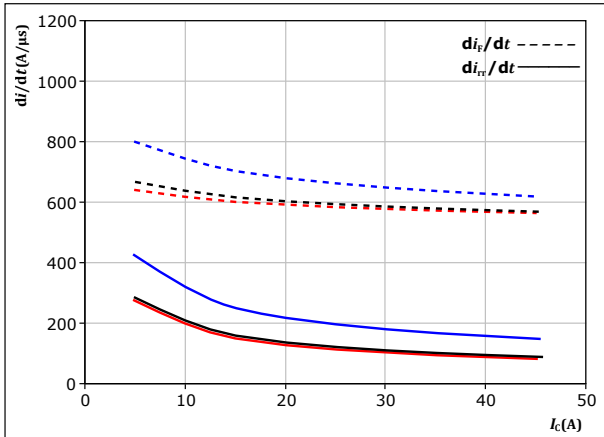
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Inverter Switching Characteristics

figure 22. FWD

Typical rate of fall of forward and reverse recovery current as a function of collector current
 $di_f/dt, di_r/dt = f(I_C)$



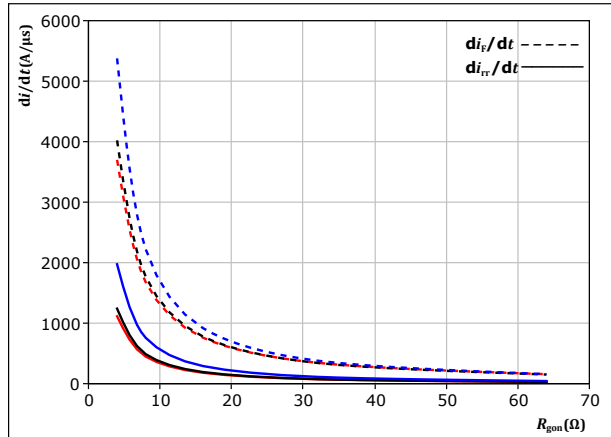
With an inductive load at

$V_{CE} = 600 \text{ V}$
 $V_{GE} = \pm 15 \text{ V}$
 $R_{gon} = 16 \text{ } \Omega$

T_j : 25 °C (blue), 125 °C (black), 150 °C (red)

figure 23. FWD

Typical rate of fall of forward and reverse recovery current as a function of turn on gate resistor
 $di_f/dt, di_r/dt = f(R_{gon})$



With an inductive load at

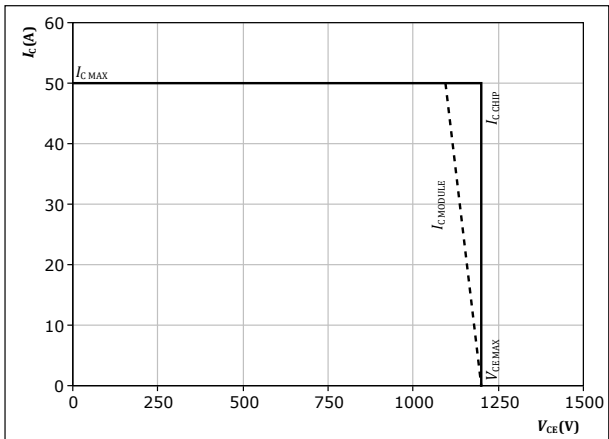
$V_{CE} = 600 \text{ V}$
 $V_{GE} = \pm 15 \text{ V}$
 $I_C = 25 \text{ A}$

T_j : 25 °C (blue), 125 °C (black), 150 °C (red)

figure 24. IGBT

Reverse bias safe operating area

$I_C = f(V_{CE})$



At $T_j = 150 \text{ } ^\circ\text{C}$
 $R_{gon} = 16 \text{ } \Omega$
 $R_{goff} = 16 \text{ } \Omega$



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Inverter Switching Definitions

figure 25. IGBT

Turn-off Switching Waveforms & definition of t_{doff} , t_{Eoff} (t_{Eoff} = integrating time for E_{off})

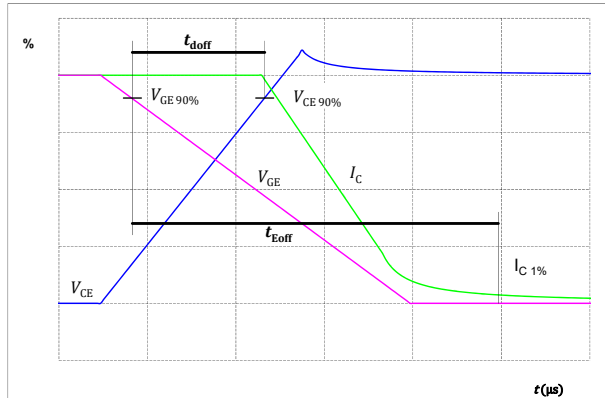


figure 26. IGBT

Turn-on Switching Waveforms & definition of t_{don} , t_{Eon} (t_{Eon} = integrating time for E_{on})

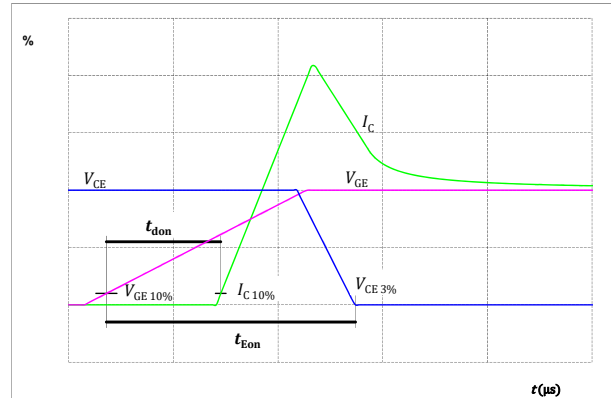


figure 27. IGBT

Turn-off Switching Waveforms & definition of t_f

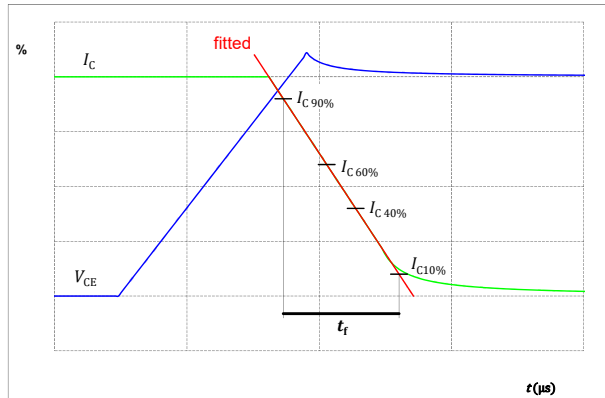
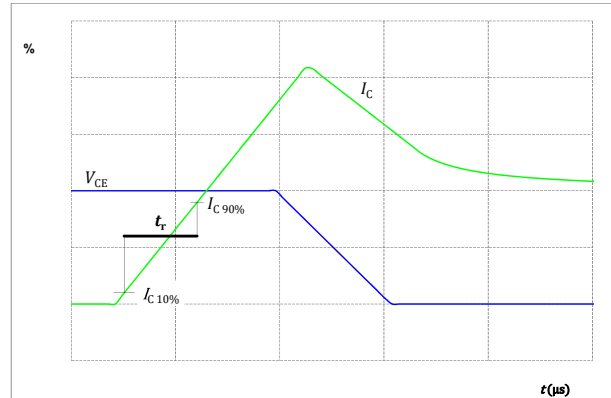


figure 28. IGBT

Turn-on Switching Waveforms & definition of t_r





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Inverter Switching Definitions

figure 29.

FWD

Turn-off Switching Waveforms & definition of t_{rr}

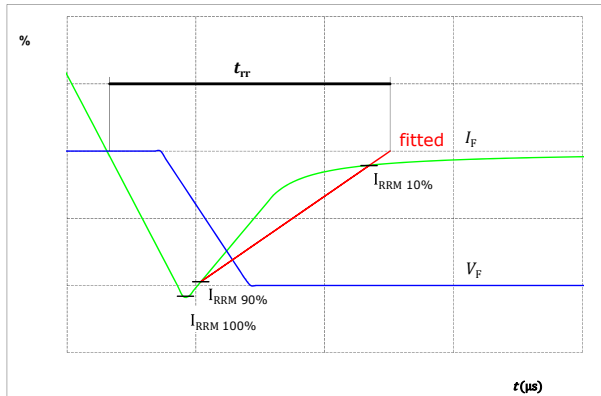
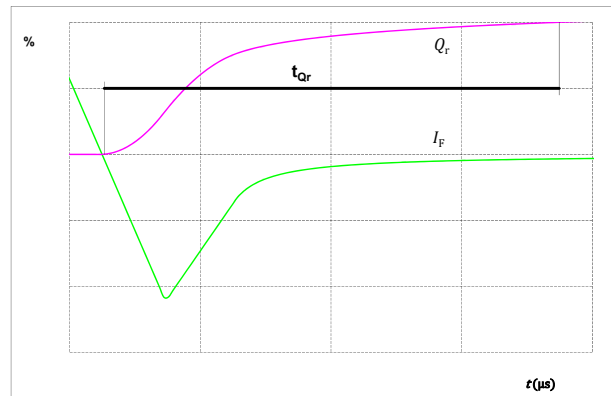


figure 30.

FWD



Turn-on Switching Waveforms & definition of t_{Qr} (t_{Qr} = integrating time for Q_r)

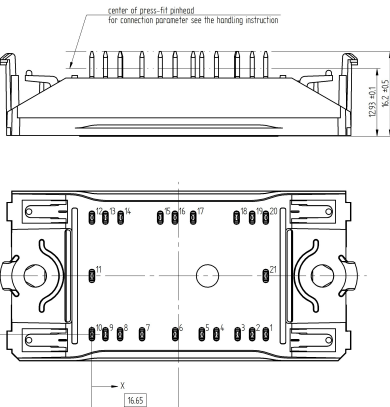




datasheet

Ordering Code	
Version	Ordering Code
Without thermal paste	10-PZ126PA025M7-P869F78Y
With thermal paste (5,2 W/mK, PTM6000HV)	10-PZ126PA025M7-P869F78Y-/7/

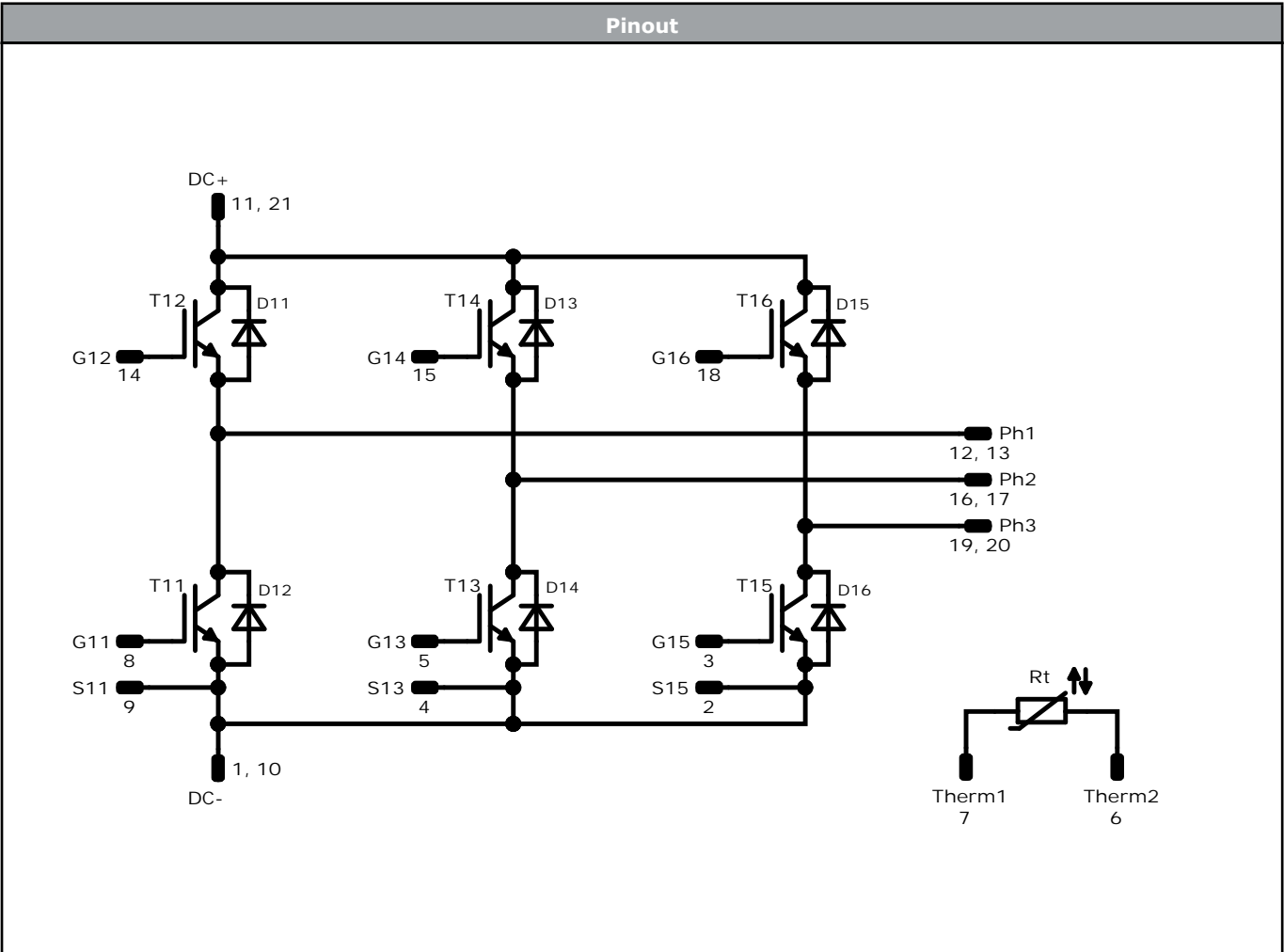
Marking							
	Text	Name		Date code	UL & VIN	Lot	Serial
		NN-NNNNNNNNNNNNN- TTTTTTVV		WWYY	UL VIN	LLLLL	SSSS
		Datamatrix	Type&Ver	Lot number	Serial	Date code	
TTTTTTVV			LLLLL	SSSS	WWYY		

Pin table [mm]				Outline	
Pin	X	Y	Function		
1	33,3	0	DC-		
2	30,7	0	S15		
3	27,9	0	G15		
4	23,85	0	S13		
5	21,05	0	G13		
6	15,95	0	Therm2		
7	9,6	0	Therm1		
8	5,4	0	G11		
9	2,6	0	S11		
10	0	0	DC-		
11	0	11,15	DC+		
12	0	22,3	Ph1		
13	2,6	22,3	Ph1		
14	5,5	22,3	G12		
15	13,1	22,3	G14		
16	15,9	22,3	Ph2		
17	19,4	22,3	Ph2		
18	27,7	22,3	G16		
19	30,7	22,3	Ph3		
20	33,3	22,3	Ph3		
21	33,3	11,15	DC+		
				Tolerance of pinpositions: ±0,5mm at the end of pins Dimension of coordinate axis is only offset without tolerance	



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10-PZ126PA025M7-P869F78Y
datasheet




Identification					
ID	Component	Voltage	Current	Function	Comment
T11, T12, T13, T14, T15, T16	IGBT	1200 V	25 A	Inverter Switch	
D11, D12, D13, D14, D15, D16	FWD	1200 V	25 A	Inverter Diode	
Rt	Thermistor			Thermistor	



Vincotech

10-PZ126PA025M7-P869F78Y
datasheet

Packaging instruction				
Standard packaging quantity (SPQ) 135	>SPQ	Standard	<SPQ	Sample
Handling instruction				
Handling instructions for <i>flow 0</i> packages see vincotech.com website.				
Package data				
Package data for <i>flow 0</i> packages see vincotech.com website.				
Vincotech thermistor reference				
See Vincotech thermistor reference table at vincotech.com website.				
UL recognition and file number				
This device is UL 1557 recognized under E192116 up to a junction temperature under switching condition $T_{j,sp}=175^{\circ}\text{C}$ and up to 3500VAC/1min isolation voltage. For more information see vincotech.com website.				

Document No.:	Date:	Modification:	Pages
10-PZ126PA025M7-P869F78Y-D1-14	4 Aug. 2025	Initial Release	

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